

#### Description

The Si2301ADS uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications.

## **General Features**

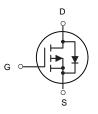
$$\begin{split} V_{DS} &= -20 V, I_D = -2.3 A \\ R_{DS(ON)} &< 115 m \, \Omega @ \, V_{GS} \text{=-}4.5 V \\ R_{DS(ON)} &< 152 m \, \Omega @ \, V_{GS} \text{=-}2.5 V \end{split}$$

## Application

PWM applications Load switch

# D





P-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
Si2301ADS	SOT-23	HXY MOSFET	3000

#### Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Symbol Parameter		Unit	
Vds	Drain-Source Voltage	-20	V	
Vgs	Gate-Source Voltage	±12	V	
lo	Drain Current-Continuous	-2.3	А	
Ідм	Drain Current-Pulsed (Note 1)	-10	А	
PD	Maximum Power Dissipation	0.7	W	
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C	
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	178	°C/W	



#### Electrical Characteristics (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	ŀ					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250µA	-20		-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±12V, $V_{DS}$ =0V	-	-	±100	nA
On Characteristics (Note 3)				1		
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250µA	-0.4	-0.7	-1	V
		$V_{GS}$ =-4.5V, $I_D$ =-2A		95	115	mΩ
Drain-Source On-State Resistance	Rds(on)	V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1.8A		125	152	mΩ
Forward Transconductance	<b>G</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-2A	4	-	-	S
Dynamic Characteristics (Note4)	<u>I</u>					
Input Capacitance	C <sub>lss</sub>		-	285	-	PF
Output Capacitance	Coss	$V_{DS}$ =-10V, $V_{GS}$ =0V,	-	58	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	32	-	PF
Switching Characteristics (Note 4)	I					
Turn-on Delay Time	t <sub>d(on)</sub>		-	9.8	-	nS
Turn-on Rise Time	tr	$V_{DD}$ =-10V, RL=5 $\Omega$	-	4.9	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-4.5V, $R_{GEN}$ =3 $\Omega$	-	20.5	-	nS
Turn-Off Fall Time	tr		-	7	-	nS
Total Gate Charge	Qg	N/ 401/1 01	-	2.9	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =-10V,I <sub>D</sub> =-2A,	-	0.45	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	$V_{GS}$ =-4.5V	-	0.75	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-2A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-2.0	А

Notes:

**1.** Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t ≤ 10 sec.

**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production



# **Typical Electrical and Thermal Characteristics**

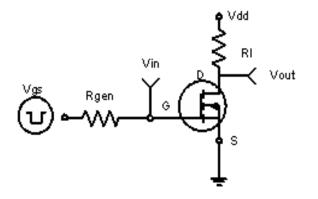


Figure 1:Switching Test Circuit

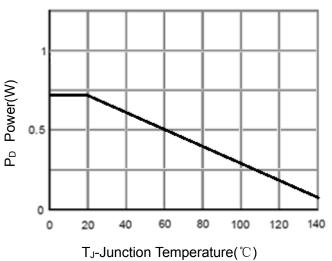
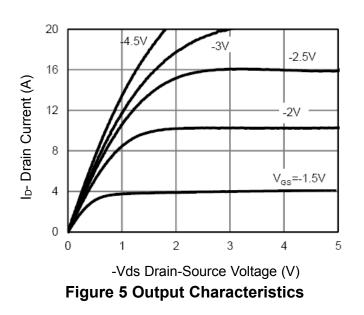


Figure 3 Power Dissipation



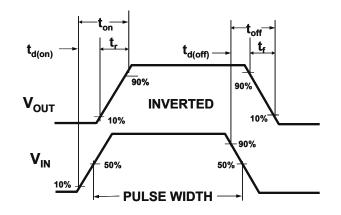


Figure 2:Switching Waveforms

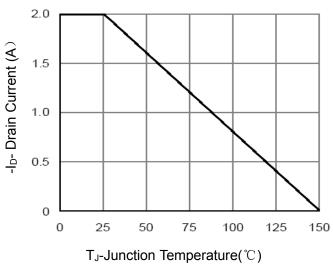


Figure 4 Drain Current

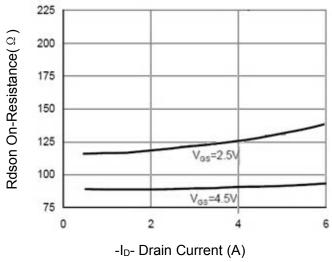
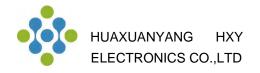
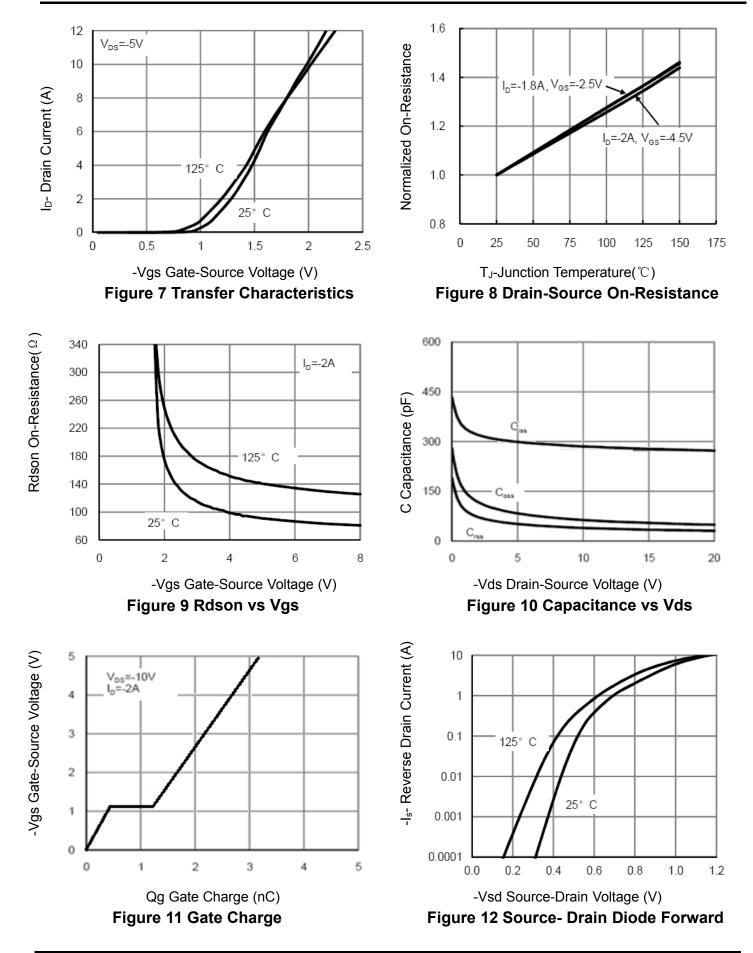


Figure 6 Drain-Source On-Resistance



## Si2301ADS P-Channel Enhancement Mode MOSFET





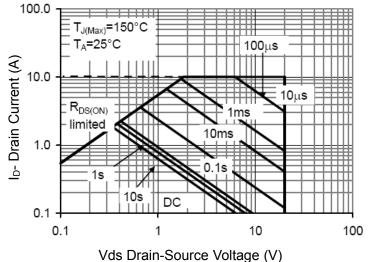


Figure 13 Safe Operation Area

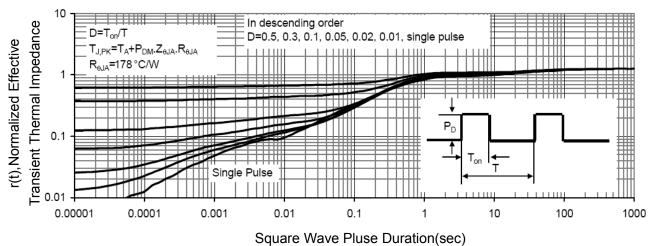
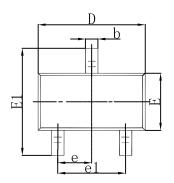
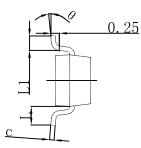


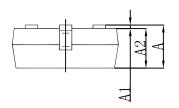
Figure 14 Normalized Maximum Transient Thermal Impedance



# **SOT-23 Package Outline Dimensions**

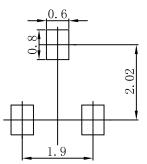






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# SOT-23 Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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